

LISTING OF THE CLAIMS:

Claims 1-14 (canceled).

15. (Previously Amended) An interdigitated capacitor, comprising:
first electrodes located on and interconnected by a first conductive layer, the first electrodes and first conductive layer comprising a metal;
a high-k dielectric layer located over and between the first electrodes and on the first conductive layer; and
an electrode layer comprising the metal and located on the high-k dielectric layer and over and between the first electrodes to form interconnected second electrodes over and between the first electrodes.

16. (Original) The interdigitated capacitor as recited in Claim 15 further comprising a first barrier layer located between the first electrodes and the dielectric layer, and a second barrier layer located between the dielectric layer and the electrode layer.

17. (Original) The interdigitated capacitor as recited in Claim 15 wherein the first electrodes have an aspect ratio ranging from about 7:1 to 10:1.

18. (Previously Amended) The interdigitated capacitor as recited in Claim 15 wherein the high-k dielectric layer is comprised of a material selected from the group consisting of:

lead zirconium titanate,

silicon nitride,
aluminum oxide, and
barium strontium titanate.

19. (Original) The interdigitated capacitor as recited in Claim 15 wherein the first electrodes and the first conductive layer are comprised of substantially the same material.

20. (Original) The interdigitated capacitor as recited in Claim 15 wherein the first electrodes, the first conductive layer, and the electrode layer are comprised of substantially the same material.

21. (Previously Amended) The interdigitated capacitor as recited in Claim 15 wherein the metal is copper.

22. (Presently Amended) The interdigitated capacitor as recited in Claim 15 ~~22~~ wherein the high-k dielectric layer comprises tantalum pentoxide.
